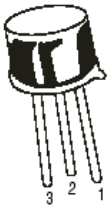
PNP High Voltage Transistor



Pin Configuration
1. Emitter
2. Base
3. Collector

Features:

- PNP Silicon High Voltage Transistor
- High speed switching and linear amplifier appliances in Military, Industrial and Commercial Equipment

Absolute Maximum Ratings:

(T_a = 25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	300	
Emitter-Base Voltage	V_{EBO}	6	
Collector Current Continuous	I_C	1	A
Base Current	I_B	0.5	
Power Dissipation at T_a = 25°C Derate above 25°C	P_D	1	W mW/°C
Power Dissipation at T_C = 25°C Derate above 25°C		10	W
Operating Temperature	T_J	200	mW/°C
Storage Temperature Range	T_{stg}	-65 to +200	°C

Thermal Resistance

Junction to Ambient	$R_{th(j-a)}$	150	°C/W
Junction to Case	$R_{th(j-c)}$	17.5	

Electrical Characteristics:

(T_a = +25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Unit
Collector Emitter Breakdown Voltage	$BV_{CEO(sus)}$*	I_C = 50mA, I_B = 0	>300	V
Collector Cut off Current	I_{CBO}	V_{CB} = 280V, I_E = 0	<50	μA
	I_{CEO}	V_{CE} = 250V, I_B = 0		
Emitter Cut off Current	I_{EBO}	V_{EB} = 6V, I_C = 0	<20	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 50mA, I_B = 5mA	<2	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 50mA, I_B = 5mA	<1.5	
DC Current Gain	h_{FE}*	I_C = 50mA, V_{CE} = 10V	30 - 120	-

Dynamic Characteristics

Small Signal Current Gain	h_{fe}	I_C = 5mA, V_{CE} = 10V, f = 1kHz	>25	-
Transition Frequency	f_T	I_C = 10mA, V_{CE} = 10V, f = 5MHz	>15	MHz
Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	<15	pF
Input Capacitance	C_{ib}	V_{EB} = V_{EBO} max., I_C = 0, f = 1MHz	<75	

*Pulsed: Pulse Width ≤30μs, Duty Cycle ≤2%

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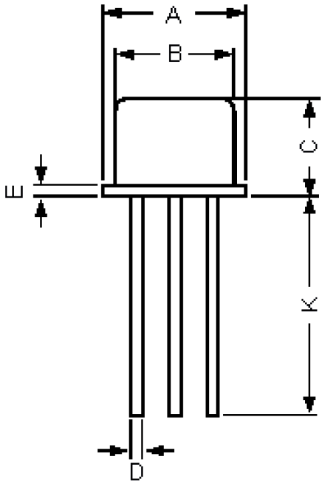
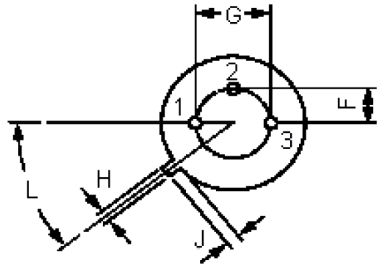
TO-39 Metal Can Package



Dim.	Min.	Max.
A	8.5	9.39
B	7.74	8.5
C	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42°	48°

Dimensions : Millimetres



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Part Number Table

Description	Part Number
RF Transistor, PNP, TO-39	2N5416